

RF Power MOSFET Transistor 150 W, 100 - 500 MHz, 28 V

Rev. V1

Features

- DMOS structure
- Lower capacitance for broadband operation
- Common source configuration

ABSOLUTE MAXIMUM RATINGS^{1, 2, 3}

Parameter	Symbol	Rating	Units
Drain-Source Voltage	V_{DS}	65	V
Gate-Source Voltage	V_{GS}	20	V
Drain-Source Current	I_{DS}	16*	A
Power Dissipation	P_D	389	W
Junction Temperature	T_J	200	°C
Storage Temperature	T_{STG}	-65 to +150	°C
Thermal Resistance	Θ_{JC}	0.45	°C/W

1. Exceeding any one or combination of these limits may cause permanent damage to this device.
2. M/A-COM does not recommend sustained operation near these maximum limits.
3. At 25°C Tcase, unless noted.

ELECTRICAL SPECIFICATIONS: 25°C

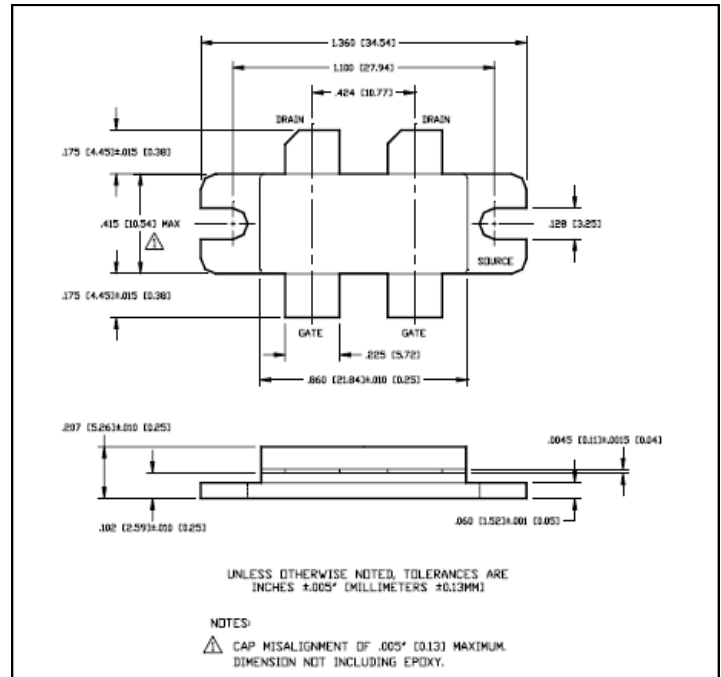
Parameter	Test Conditions	Units	Min.	Max.
Drain-Source Breakdown Voltage	$V_{GS} = 0.0 \text{ V}$, $I_{DS} = 20.0 \text{ mA}^*$	BV_{DSS}	65	—
Drain-Source Leakage Current	$V_{DS} = 28.0 \text{ V}$, $V_{GS} = 0.0 \text{ V}^*$	I_{DSS}	—	4.0
Gate-Source Leakage Current	$V_{GS} = 20 \text{ V}$, $V_{DS} = 0.0 \text{ V}^*$	I_{GSS}	—	4.0
Gate Threshold Voltage	$V_{DS} = 10.0 \text{ V}$, $I_{DS} = 400.0 \text{ mA}^*$	$V_{GS(TH)}$	2.0	6.0
Forward Transconductance	$V_{DS} = 10.0 \text{ V}$, $I_{DS} = 4000.0 \text{ mA}$, $\Delta V_{GS} = 1.0 \text{ V}$, 80µs pulse*	G_M	2.0	—
Input Capacitance	$V_{DS} = 28.0 \text{ V}$, $F = 1.0 \text{ MHz}^*$	C_{ISS}	—	180
Output Capacitance	$V_{DS} = 28.0 \text{ V}$, $F = 1.0 \text{ MHz}^*$	C_{OSS}	—	120
Reverse Capacitance	$V_{DS} = 28.0 \text{ V}$, $F = 1.0 \text{ MHz}^*$	C_{RSS}	—	32
Power Gain	$V_{DD} = 28.0 \text{ V}$, $I_{DQ} = 400.0 \text{ mA}$, $P_{OUT} = 150.0 \text{ W}$, $F = 500 \text{ MHz}$	G_P	8	—
Drain Efficiency	$V_{DD} = 28.0 \text{ V}$, $I_{DQ} = 400.0 \text{ mA}$, $P_{OUT} = 150.0 \text{ W}$, $F = 500 \text{ MHz}$	η_D	55	—
Load Mismatch Tolerance	$V_{DD} = 28.0 \text{ V}$, $I_{DQ} = 400.0 \text{ mA}$, $P_{OUT} = 150.0 \text{ W}$, $F = 500 \text{ MHz}$	VSWR-T	—	10:1**

Notes:

* Per side

** At all phase angles

Package Outline

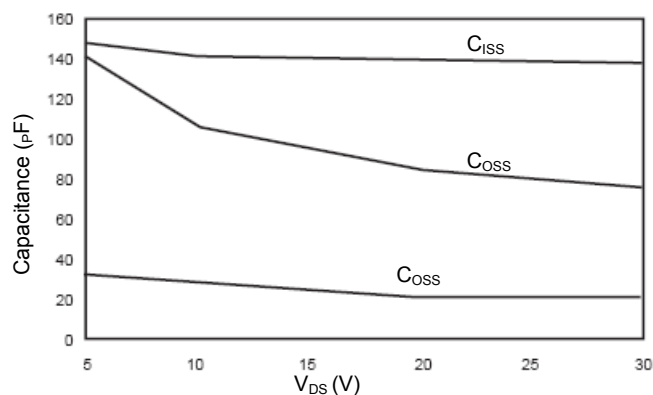


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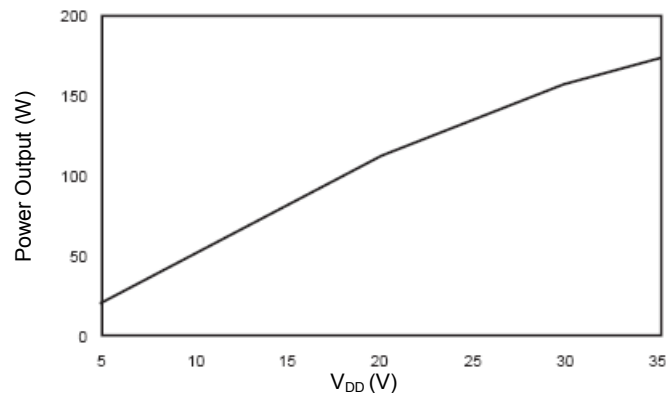
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Typical Broadband Performance Curves

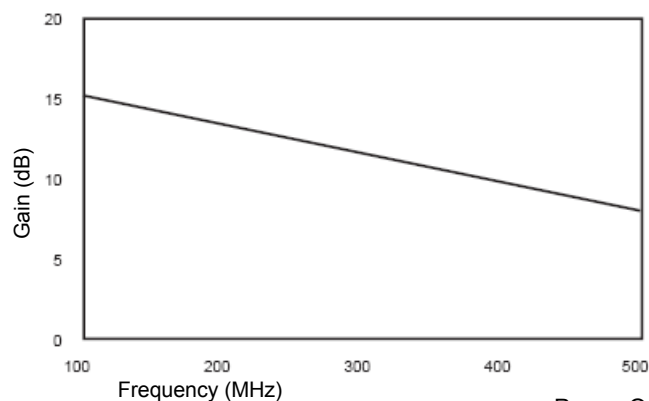
Capacitance vs Voltage
 $F=1.0\text{ MHz}$



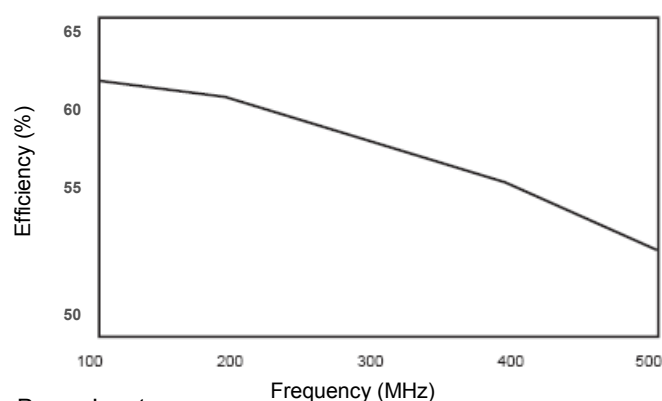
Power Output vs Voltage
 $P_{IN}=24\text{ W}$ $I_{DQ}=400\text{ mA}$ $F=500\text{ MHz}$



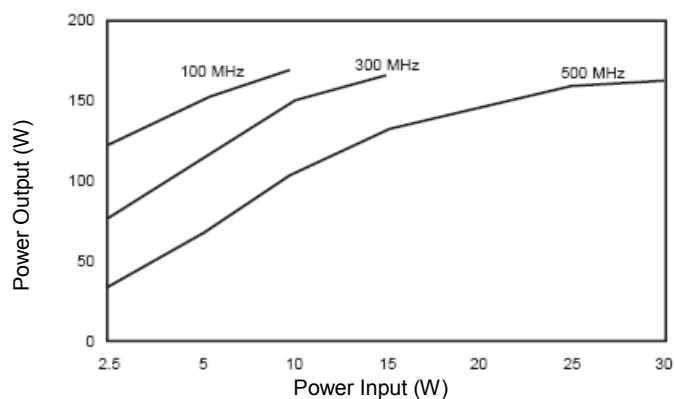
Gain vs Frequency
 $V_{DD}=28\text{ V}$ $P_{OUT}=100\text{ W}$ $I_{DQ}=400\text{ mA}$



Efficiency vs Frequency
 $V_{DD}=28\text{ V}$ $I_{DQ}=400\text{ mA}$ $P_{OUT}=150\text{ W}$



Power Output vs Power Input
 $V_{DD}=28\text{ V}$ $I_{DQ}=400\text{ mA}$

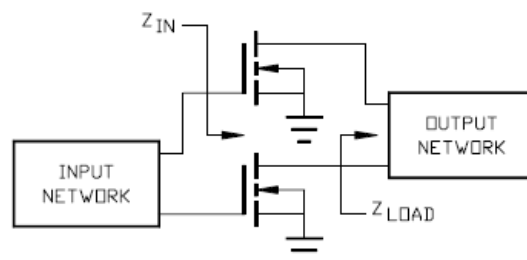


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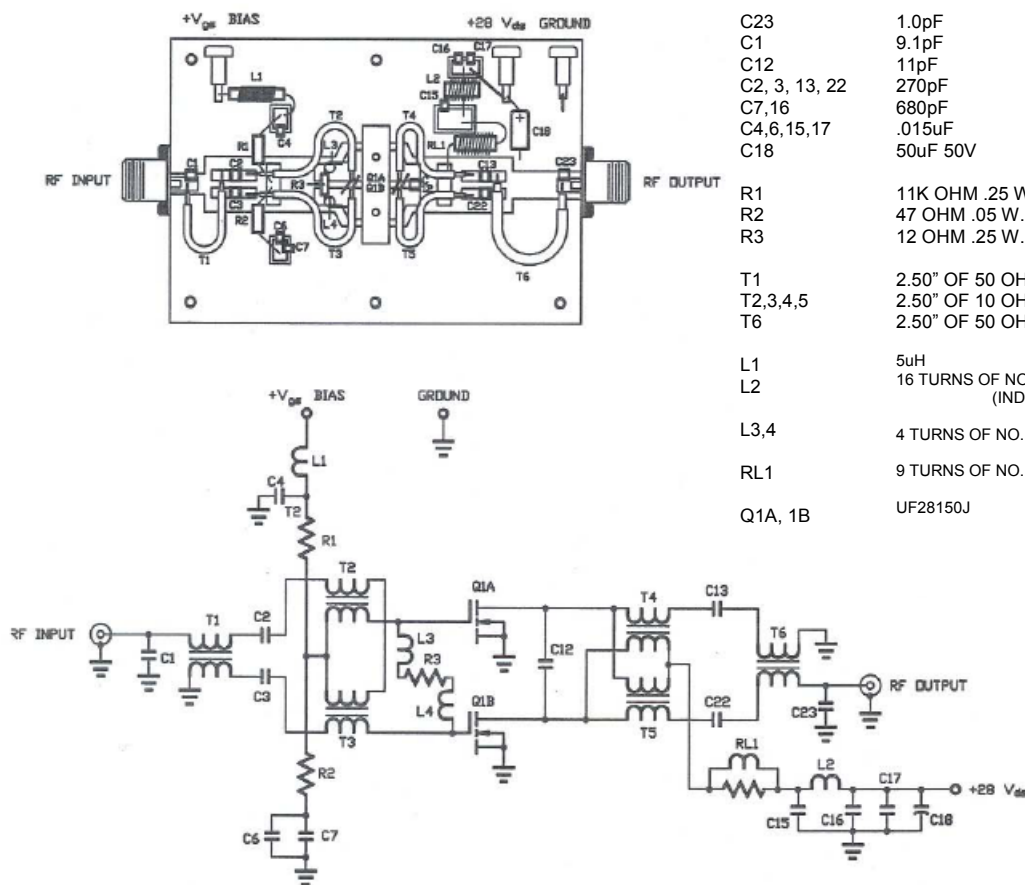
TYPICAL OPTIMUM DEVICE IMPEDANCES

F (MHz)	$Z_{IN} (\Omega)$	$Z_{LOAD} (\Omega)$
100	$3.7 - j5.9$	$3.0 - j0.7$
300	$2.7 - j5.9$	$2.6 - j0.55$
500	$2.5 - j2.9$	$2.5 - j0.5$
$V_{DD} = 28V$, $I_{DQ} = 400mA$, $P_{OUT} = 150W$		



PARTS LIST

C23	1.0pF
C1	9.1pF
C12	11pF
C2, 3, 13, 22	270pF
C7,16	680pF
C4,6,15,17	.015uF
C18	50uF 50V
R1	11K OHM .25 W. 10%
R2	47 OHM .05 W. 10%
R3	12 OHM .25 W. 10%
T1	2.50" OF 50 OHM (.85" OD) SEMI-RIGID CABLE
T2,3,4,5	2.50" OF 10 OHM (.70" OD) SEMI-RIGID CABLE
T6	2.50" OF 50 OHM (.141" OD) SEMI-RIGID CABLE
L1	5uH
L2	16 TURNS OF NO. 18 AWG ON TOROID CORE (INDIANA GENERAL F6278-Q1)
L3,4	4 TURNS OF NO. 18 AWG ON .125 DIAMETER
RL1	9 TURNS OF NO. 18 AWG ON 15 OHM 2 W. 10% RESISTOR
Q1A, 1B	UF28150J



HANDLING PROCEDURES: STATIC SENSITIVITY

Please observe the following precautions to avoid damage:

DMOS devices are sensitive to electrostatic discharge (ESD) and can be damaged by static electricity. Proper ESD control techniques should be used when handling these devices.

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